

MRF313 MRF313A

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CASE 305A-01, STYLE 1

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HIGH FREQUENCY TRANSISTOR

NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	150	mAdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 35	Watts mW/ $^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	28.5	$^\circ\text{C/W}$

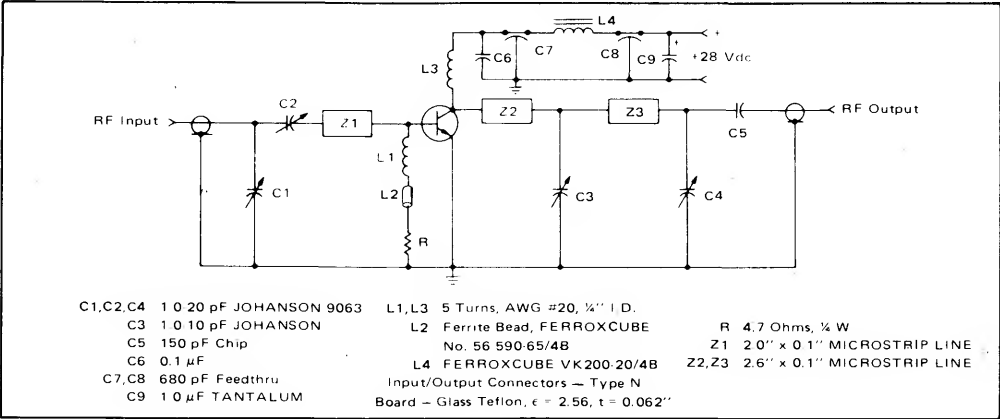
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 5.0\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	35	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1\text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	35	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 1.0\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 20\text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	—	1.0	mAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	20	60	150	—
SMALL SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 100\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 200\text{ MHz}$)	f_T	—	2.5	—	GHz
Output Capacitance ($V_{CB} = 28\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	3.5	5.0	pF
FUNCTIONAL TEST					
Common-Emitter Amplifier Power Gain(1) ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 1.0\text{ W}$, $f = 400\text{ MHz}$)	G_{pe}	15	16	—	dB
Collector Efficiency ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 1.0\text{ W}$, $f = 400\text{ MHz}$)	η	—	45	—	%
Series Equivalent Input Impedance ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 1.0\text{ W}$, $f = 400\text{ MHz}$)	Z_{in}	—	6.4 - j4.8	—	Ohms
Series Equivalent Output Impedance ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 1.0\text{ W}$, $f = 400\text{ MHz}$)	Z_{out}	—	75 - j45	—	Ohms

(1) Class C

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FIGURE 1 - 400 MHz POWER GAIN TEST CIRCUIT



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